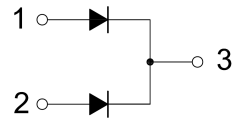
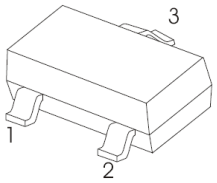
迈拓电子
MAITUO ELECTRONIC

DAN202 SWITCHING DIODE





SOT-23

FEATURES

- High Speed
- High Reliability
- Suitable for High Packing Density Layout

APPLICATIONS

- High Speed Switching

MARKING: N

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_R	DC Blocking Voltage	80	V
I_O	Continuous Forward Current	100	mA
I_{FM}	Peak Forward Current	300	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current@t=8.3ms	2	A
P_D	Power Dissipation	250	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	500	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	I_R=100μA	80			V
Reverse current	I_R	V_R=70V			0.1	μA
Forward voltage	V_F	I_F=100mA			1.2	V
Total capacitance	C_{tot}	V_R=6V,f=1MHz			3.5	pF
Reverse recovery time	t_{rr}	I_F= I_R=5mA, V_R=6V			4	ns

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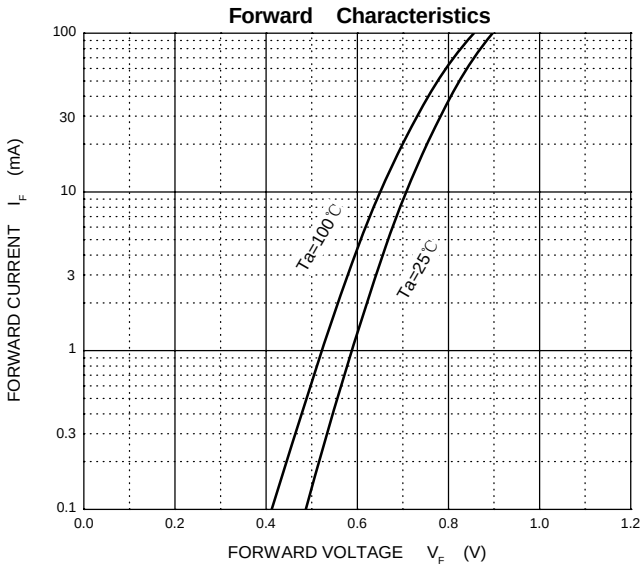
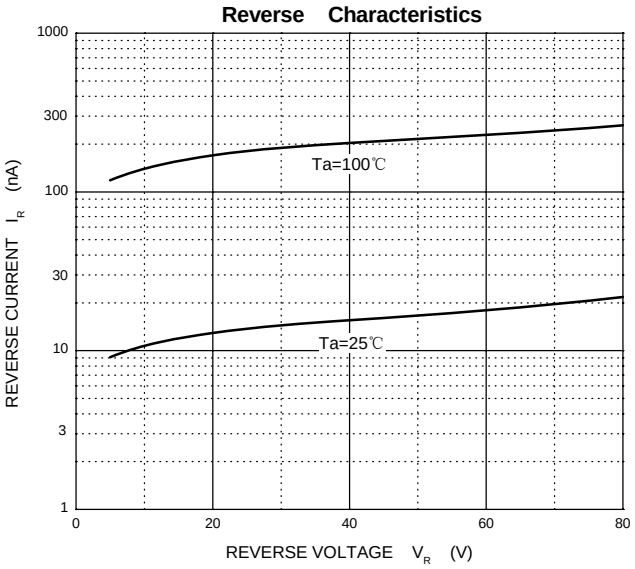
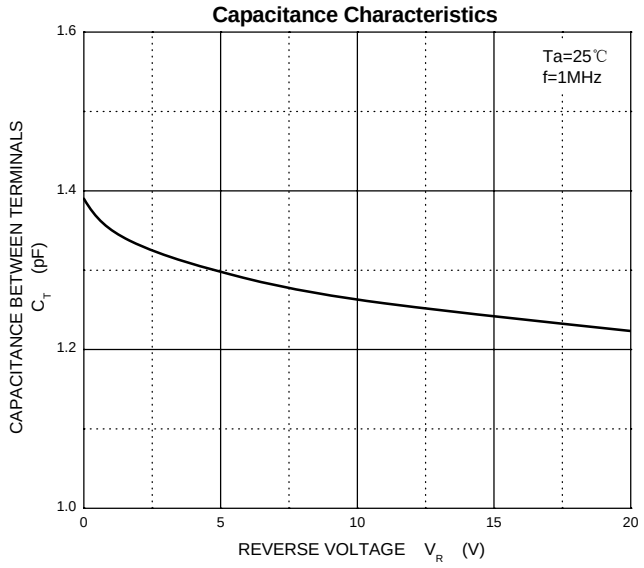
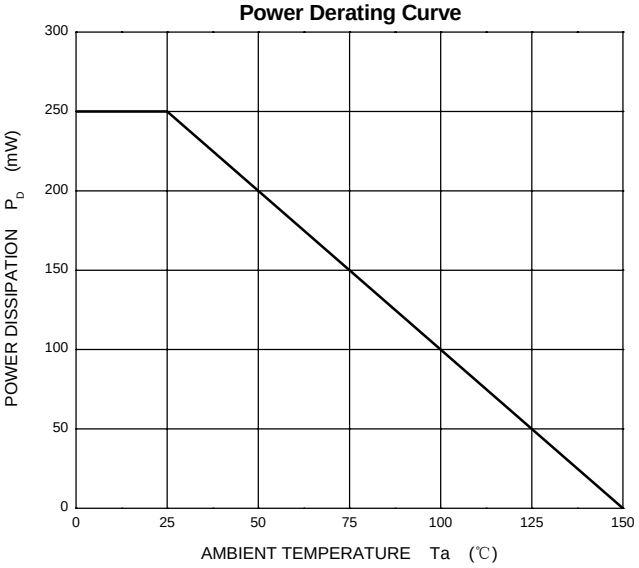
Typical Characteristics









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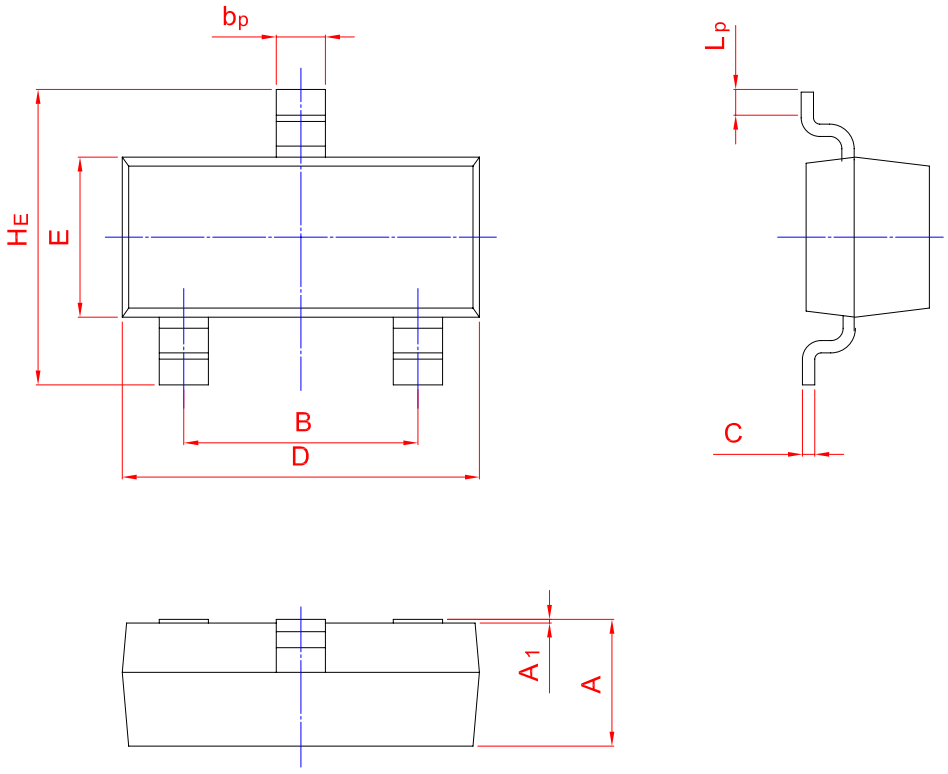
PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT-23**



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20